

# NPN SILICON RF POWER TRANSISTOR

## DESCRIPTION:

The **ASI BAM80** is Designed for VHF AM power amplifier Applications in the range of 100 to 150 MHz.

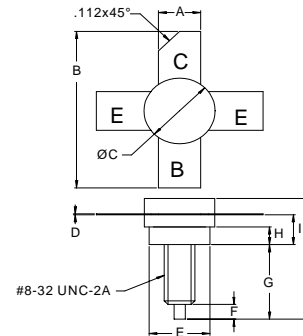
## FEATURES:

- Common Emitter
- $P_G = 6.0$  dB at 20 W/150 MHz
- **Omnigold™** Metalization System

## MAXIMUM RATINGS

$I_C$	8.5 A
$V_{CES}$	60 V
$V_{CEO}$	35 V
$V_{EBO}$	4.0 V
$P_{DISS}$	85 W
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +200 °C
$\theta_{JC}$	2.0 °C/W

## PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

## CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 50$ mA	35			V
$BV_{CES}$	$I_C = 20$ mA	60			V
$BV_{EBO}$	$I_E = 5.0$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			2.0	mA
$I_{CES}$	$V_{CE} = 30$ V $T_C = 125^\circ\text{C}$			10	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		---	---
$C_{cb}$	$V_{CB} = 28$ V $f = 1.0$ MHz			75	pF
$P_G$ $\eta_c$ VSWR	$V_{CE} = 13.5$ V $P_{OUT} = 20$ W $f = 150$ MHz	6.0 30:1	65		dB % ---

This datasheet has been downloaded from:

[www.DatasheetCatalog.com](http://www.DatasheetCatalog.com)

Datasheets for electronic components.